

**Amendments to the Specifications:**

Amend paragraph [0005] of the published specification as follows:

[0005] Growing the p-conducting layer onto an electrically conductive substrate, which would enable current to be impressed over the entire lateral cross section of the p-conducting layer, does not lead to an economically tenable result. The reasons for this can be explained as follows. Firstly, the production of electrically conductive lattice-matched substrates (e.g. GaN substrates) for the growth of GaN-based layers is associated with a high technical outlay; secondly, growing p-doped GaN-based layers onto non-lattice-matched substrates that are suitable for undoped and n-doped GaN compounds does not lead to a crystal quality that is adequate for a light-emitting diode.